

# **RGW80TS65**

### 650V 40A Field Stop Trench IGBT

| V <sub>CES</sub>            | 650V |
|-----------------------------|------|
| I <sub>C (100°C)</sub>      | 40A  |
| V <sub>CE(sat) (Typ.)</sub> | 1.5V |
| $P_D$                       | 214W |

## ● Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

### Applications

**PFC** 

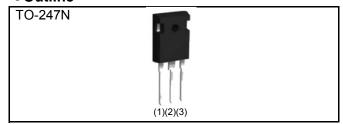
**UPS** 

Welding

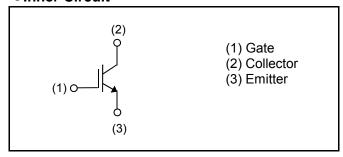
Solar Inverter

ΙH

#### Outline



### ●Inner Circuit



Packaging Specifications

| i deliaging eperineurene |                           |           |  |  |  |
|--------------------------|---------------------------|-----------|--|--|--|
|                          | Packaging                 | Tube      |  |  |  |
|                          | Reel Size (mm)            | -         |  |  |  |
| Typo                     | Tape Width (mm)           | -         |  |  |  |
| Type                     | Basic Ordering Unit (pcs) | 450       |  |  |  |
|                          | Packing Code              | C11       |  |  |  |
|                          | Marking                   | RGW80TS65 |  |  |  |

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

| Parameter                      |                        | Symbol             | Value       | Unit |
|--------------------------------|------------------------|--------------------|-------------|------|
| Collector - Emitter Voltage    |                        | V <sub>CES</sub>   | 650         | V    |
| Gate - Emitter Voltage         |                        | V <sub>GES</sub>   | ±30         | V    |
| Collector Current              | T <sub>C</sub> = 25°C  | I <sub>C</sub>     | 78          | А    |
|                                | T <sub>C</sub> = 100°C | 100°C              |             | А    |
| Pulsed Collector Current       |                        | I <sub>CP</sub> *1 | 160         | А    |
| Power Dissipation              | T <sub>C</sub> = 25°C  | P <sub>D</sub>     | 214         | W    |
|                                | T <sub>C</sub> = 100°C | P <sub>D</sub>     | 107         | W    |
| Operating Junction Temperature |                        | Tj                 | -40 to +175 | °C   |
| Storage Temperature            |                        | T <sub>stg</sub>   | -55 to +175 | °C   |

<sup>\*1</sup> Pulse width limited by T<sub>imax</sub>.

### ●Thermal Resistance

| Parameter                               | Symbol            | Values |      |      | Unit  |
|---|-------------------|--------|------|------|-------|
| - Faranietei                            |                   | Min.   | Тур. | Max. | Offic |
| Thermal Resistance IGBT Junction - Case | $R_{\theta(j-c)}$ | -      | -    | 0.70 | °C/W  |

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

| Parameter                                 | Symbol               | Conditions  | Values |             |      | Unit  |
|---|----------------------|---|--------|-------------|------|-------|
| r ai ai nietei                            | Syllibol             | Conditions  | Min.   | Тур.        | Max. | Offic |
| Collector - Emitter Breakdown<br>Voltage  | BV <sub>CES</sub>    | $I_{C} = 10 \mu A, V_{GE} = 0 V$                                | 650    | -           | -    | V     |
| Collector Cut - off Current               | I <sub>CES</sub>     | V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V                    | 1      | 1           | 10   | μΑ    |
| Gate - Emitter Leakage Current            | I <sub>GES</sub>     | $V_{GE} = \pm 30V, V_{CE} = 0V$                                 | -      | -           | ±200 | nA    |
| Gate - Emitter Threshold<br>Voltage       | $V_{\text{GE(th)}}$  | $V_{CE} = 5V, I_{C} = 26.0 \text{mA}$                           | 5.0    | 6.0         | 7.0  | ٧     |
| Collector - Emitter Saturation<br>Voltage | V <sub>CE(sat)</sub> | $I_C = 40A$ , $V_{GE} = 15V$<br>$T_j = 25$ °C<br>$T_j = 175$ °C | -      | 1.5<br>1.85 | 1.9  | ٧     |

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

| Daramatar                        | Cymphal             | Conditions                                    | Values |         |      | Linit |
|----------------------------------|---------------------|---|--------|---------|------|-------|
| Parameter                        | Symbol Conditions   | Min.  | Тур.   | Max.    | Unit |       |
| Input Capacitance                | C <sub>ies</sub>    | V <sub>CE</sub> = 30V                         | -      | 3320    | -    |       |
| Output Capacitance               | C <sub>oes</sub>    | V <sub>GE</sub> = 0V                          | -      | 83      | -    | pF    |
| Reverse Transfer Capacitance     | C <sub>res</sub>    | f = 1MHz                                      | -      | 60      | -    |       |
| Total Gate Charge                | $Q_g$               | V <sub>CE</sub> = 400V                        | -      | 110     | -    |       |
| Gate - Emitter Charge            | $Q_{ge}$            | I <sub>C</sub> = 40A                          | -      | 23      | -    | nC    |
| Gate - Collector Charge          | $Q_{gc}$            | V <sub>GE</sub> = 15V                         | -      | 41      | -    |       |
| Turn - on Delay Time             | t <sub>d(on)</sub>  | I <sub>C</sub> = 40A, V <sub>CC</sub> = 400V  | -      | 44      | -    |       |
| Rise Time                        | t <sub>r</sub>      | $V_{GE} = 15V, R_{G} = 10\Omega$              | -      | 17      | -    |       |
| Turn - off Delay Time            | t <sub>d(off)</sub> | T <sub>j</sub> = 25°C                         | -      | 143     | -    | ns    |
| Fall Time                        | t <sub>f</sub>      | Inductive Load                                | -      | 34      | -    |       |
| Turn - on Switching Loss         | E <sub>on</sub>     | *E <sub>on</sub> includes diode               | -      | 0.76    | -    |       |
| Turn - off Switching Loss        | E <sub>off</sub>    | reverse recovery                              | -      | 0.72    | -    | mJ    |
| Turn - on Delay Time             | t <sub>d(on)</sub>  | I <sub>C</sub> = 40A, V <sub>CC</sub> = 400V  | -      | 41      | -    |       |
| Rise Time                        | t <sub>r</sub>      | $V_{GE} = 15V, R_G = 10\Omega$                | -      | 18      | -    | no    |
| Turn - off Delay Time            | $t_{d(off)}$        | T <sub>j</sub> = 175°C                        | -      | 158     | -    | ns    |
| Fall Time                        | t <sub>f</sub>      | Inductive Load                                | -      | 74      | -    |       |
| Turn - on Switching Loss         | E <sub>on</sub>     | *E <sub>on</sub> includes diode               | -      | 0.76    | -    | m l   |
| Turn - off Switching Loss        | E <sub>off</sub>    | reverse recovery                              | -      | 0.91    | -    | mJ    |
|                                  |                     | I <sub>C</sub> = 160A, V <sub>CC</sub> = 520V |        |         |      |       |
| Reverse Bias Safe Operating Area | RBSOA               | V <sub>P</sub> = 650V, V <sub>GE</sub> = 15V  | FU     | LL SQUA | RE   | -     |
| 1                                |                     | $R_G = 100\Omega, T_j = 175^{\circ}C$         |        |         |      |       |

### **•**Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

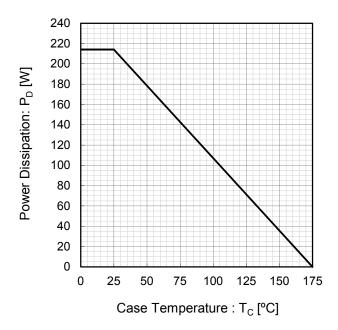


Fig.2 Collector Current vs. Case Temperature

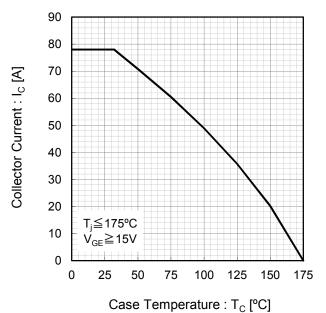


Fig.3 Forward Bias Safe Operating Area

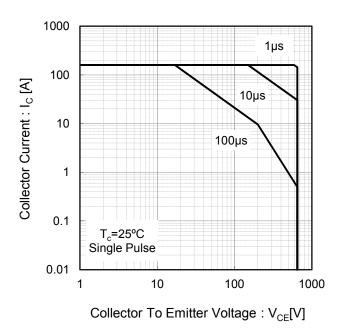
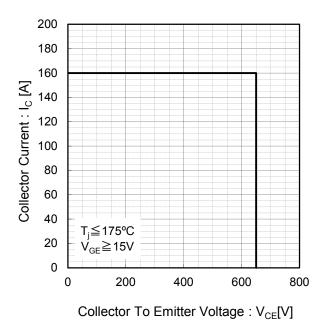


Fig.4 Reverse Bias Safe Operating Area



### • Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

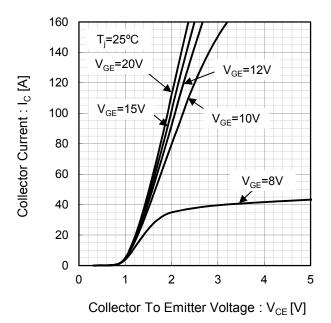
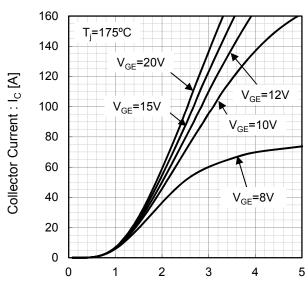


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.7 Typical Transfer Characteristics

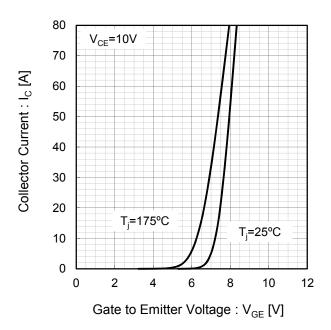
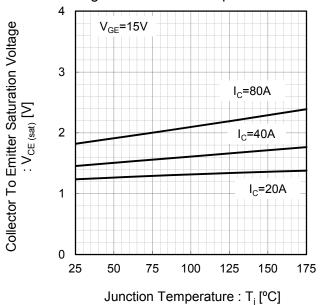
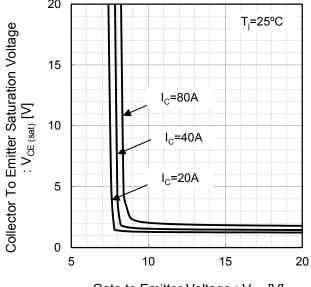


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



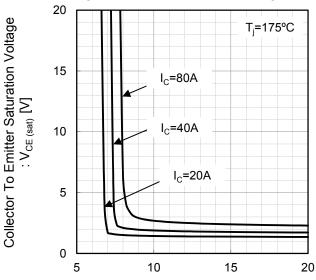
### **•**Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate to Emitter Voltage :  $V_{GE}[V]$ 

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate to Emitter Voltage : V<sub>GE</sub> [V]

Fig.11 Typical Switching Time vs. Collector Current

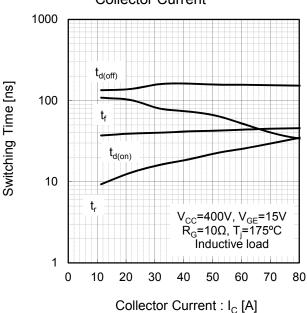
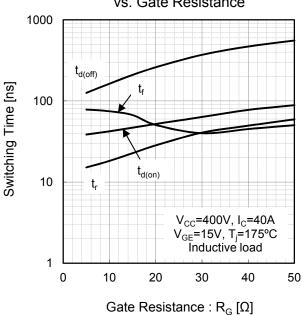


Fig.12 Typical Switching Time vs. Gate Resistance

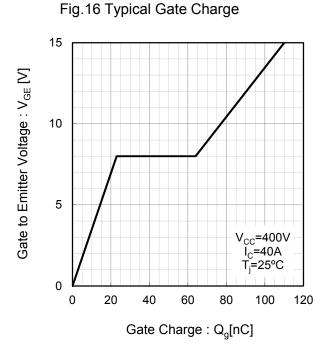


### **•**Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V R<sub>G</sub>=10 $\Omega$ , T<sub>j</sub>=175°C Inductive load 0.01 50 0 10 20 30 40 60 70 80 Collector Current : I<sub>C</sub> [A]

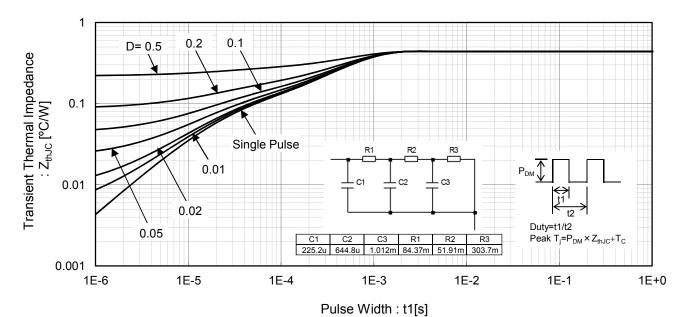
Fig.14 Typical Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 E<sub>on</sub> 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=40A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 10 30 40 0 20 50 Gate Resistance :  $R_G [\Omega]$ 

Fig.15 Typical Capacitance vs.
Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V<sub>GE</sub>=0V =25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage :  $V_{CE}[V]$ 



### • Electrical Characteristic Curves

Fig.17 Typical IGBT Transient Thermal Impedance



### •Inductive Load Switching Circuit and Waveform

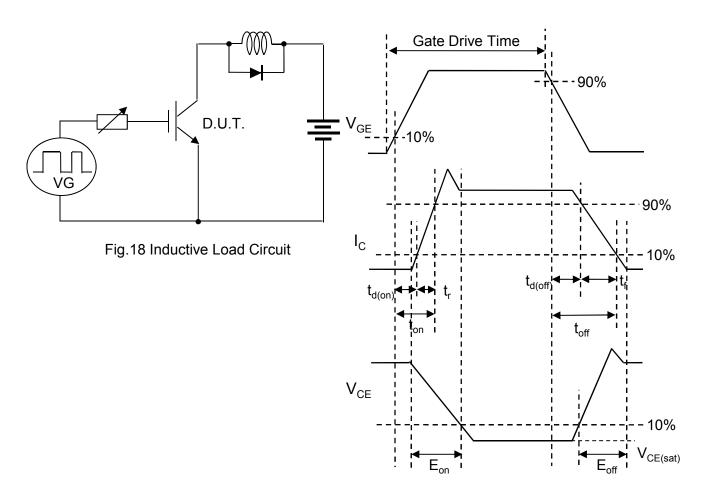


Fig.19 Inductive Load Waveform

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